

Vishay Semiconductors

# High Power Infrared Emitting Diode, 940 nm, GaAIAs/GaAs



### DESCRIPTION

TSAL5100 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power, molded in a blue-gray plastic package.

### FEATURES

- Package type: leaded
- Package form: T-134
- Dimensions (in mm):  $\varnothing$  5
- Leads with stand-off
- Peak wavelength:  $\lambda_p = 940 \text{ nm}$
- · High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 10^{\circ}$
- · Low forward voltage
- Suitable for high pulse current operation
- · Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

#### **APPLICATIONS**

- · Infrared remote control units with high power reqirements
- Free air transmission systems
- · Infrared source for optical counters and card readers
- IR source for smoke detectors
- · Smoke-automatic fire detectors

## **PRODUCT SUMMARY**

PRODUCT SUMMART				
COMPONENT	l <sub>e</sub> (mW/sr)	φ <b>(deg)</b>	λ <sub>P</sub> (nm)	t <sub>r</sub> (ns)
TSAL5100	130	± 10	940	800

#### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMAT	ΓΙΟΝ		
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSAL5100	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾

#### Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		١ <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1.5	А	
Power dissipation		Pv	160	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R <sub>thJA</sub>	230	K/W	

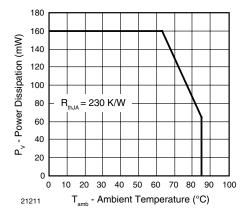
#### Note

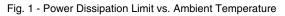
Tamb = 25 °C, unless otherwise specified





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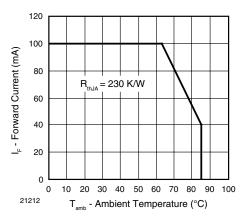


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	V <sub>F</sub>		1.35	1.6	V
	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	V <sub>F</sub>		2.6	3	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		- 1.8		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μΑ
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	Cj		25		pF
Radiant intensity	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	l <sub>e</sub>	80	130	400	mW/sr
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	l <sub>e</sub>	650	1000		mW/sr
Radiant power	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	φ <sub>e</sub>		35		mW
Temperature coefficient of $\phi_{\text{e}}$	I <sub>F</sub> = 20 mA	TKφe		- 0.6		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I <sub>F</sub> = 100 mA	λ <sub>p</sub>		940		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		50		nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	ΤΚλ <sub>ρ</sub>		0.2		nm/K
Rise time	I <sub>F</sub> = 100 mA	tr		800		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		800		ns
Virtual source diameter	method: 63 % encircled energy	d		3.7		mm

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified

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## **BASIC CHARACTERISTICS**

 $T_{amb} = 25 \ ^{\circ}C$ , unless otherwise specified

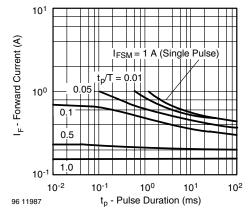


Fig. 3 - Pulse Forward Current vs. Pulse Duration

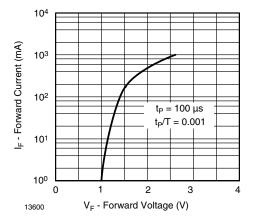


Fig. 4 - Forward Current vs. Forward Voltage

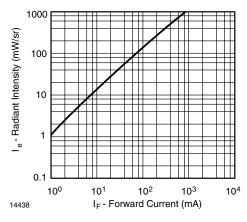


Fig. 5 - Radiant Intensity vs. Forward Current

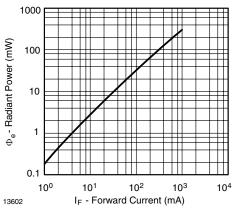


Fig. 6 - Radiant Power vs. Forward Current

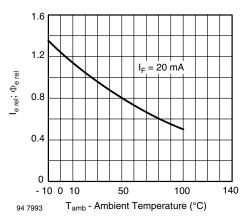


Fig. 7 - Rel. Radiant Intensity/Power vs. Ambient Temperature

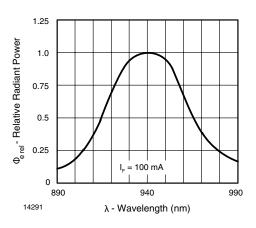


Fig. 8 - Relative Radiant Power vs. Wavelength



## **TSAL5100**

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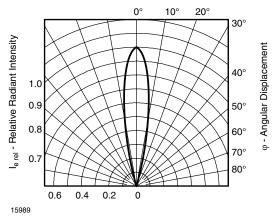
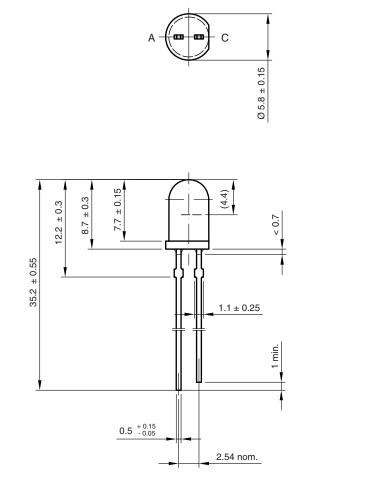
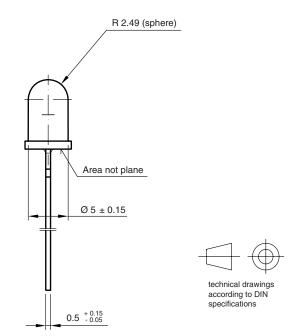


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement







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